

AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph number 6 of the specification with the following replacement paragraph:

[0006] In accordance with another aspect of the invention, a device, such as a stent, is provided having a surface and a TiN_xC_y compound deposited on at ~~least~~ least a region of the surface of the device. In accordance with another aspect of the invention, a device, such as a stent, is provided having a surface and a TiN_xC_y compound implanted at a depth within at least a region of the surface of the stent.

Please replace paragraph 8 of the specification with the following replacement paragraph:

[0008] In accordance with another aspect of the invention, a method of modifying a surface of a device, such as a stent is provided, which method comprises implanting Ti, N, or TiN into the surface of the stent and forming a layer of the TiN_xO_y compound over the areas where Ti, N, or TiN has been implanted.

Please replace paragraph 17 of the specification with the following replacement paragraph:

[0017] Figure 2B illustrates nitrogen ~~implanted a im-~~ planted within surface 16, as indicated by region 20. It should be noted that the presence of a titanium grid in the reaction chamber during the implantation procedure of nitrogen does not lead to any significant sputtering of the titanium from the grid and onto stent 10 as the nitrogen ions should be essentially incapable of sputtering the titanium off the grid.

Please replace paragraph 21 of the specification with the following replacement paragraph:

[0021] The negative voltage applied to stent 10 can have a frequency of up to, for example, 500 KHz and a width of 70 to about 200 microseconds. In one embodiment, as illustrated in Figure 2C1, a TiN_xO_y layer 22 is formed on the nitrogen or titanium region 20. In accordance with another embodiment, the nitrogen gas can be introduced into the chamber prior to the introduction of the combination of the oxygen and nitrogen gases. Accordingly, region 20 may include traces of TiN or alternatively, as illustrated in Figure 2C2, a layer of TiN, as illustrated by reference number 24, may be implanted in surface 16 followed by formation of TiN_xO_y layer 22 when oxygen is introduced in the chamber. In ~~yet~~ an alternative embodiment, as illustrated in Figure 2C3, some of the TiN_xO_y can be implanted within surface 16, as illustrated by region 22b, in addition to having TiN_xO_y deposited on surface 16, as illustrated by region 22a. Region 22b can be from about 500 Å to about 2000 Å in depth. As is understood by one of ordinary skill in the art, a variety of modifications can be made to the process parameters so as to achieve a particular cross-sectional topography.

Please replace paragraph 25 of the specification with the following replacement paragraph:

[0025] Electrode 36 can be made from of any suitable electrically conductive material including, but not limited to, steel, copper, chromium, nickel, ~~wolfram~~ tungsten, iron, and similar materials. A first power source 38, electrically coupled to electrode 36 via electrical feedthrough port 40, can apply negative voltage pulses to electrode 36.